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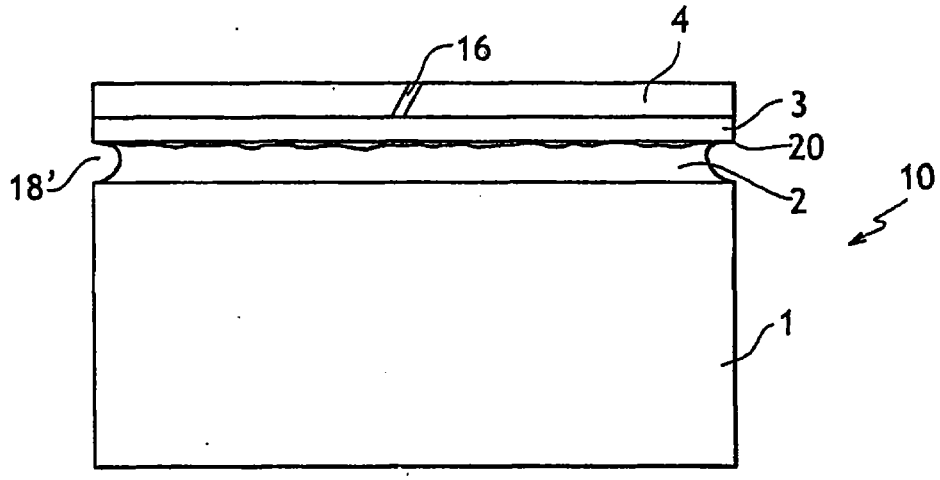
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As printed

(54) Title: PRODUCTION OF A STRUCTURE COMPRISING A PROTECTIVE LAYER AGAINST CHEMICAL TREATMENT

(54) Titre : REALISATION D'UNE STRUCTURE COMPRENANT UNE COUCHE PROTEGEANT CONTRE DES TRAITEMENTS CHIMIQUES



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(57) Abstract: The invention relates to a method for producing a multi-layer structure which comprises a buried layer and is used for electronic, optic and optoelectronic engineering consisting in a) forming the layers of the structure including the buried layer, and in b) chemically treating said structure using chemical species for substantially engraving the buried layer material. The stage a) consists in forming, a buried protective layer which is arranged on the buried layer and made of a material selected such that it is sufficiently resistant to the chemical attack of the treating chemical species used at the stage b), thereby blocking possible access of said chemical species to the buried layer therethrough. The use of said method for producing structure for electronic, optic and optoelectronic engineering is also disclosed.

(57) Abrégé : Procédé de réalisation d'une structure à plusieurs couches destinée à l'électronique, l'optique ou l'optoélectronique comprenant une couche enterrée. Le procédé comprend les étapes successives suivantes : a) formation de couches de la structure, comprenant la formation de la couche enterrée ; b) traitement chimique de la structure employant des espèces chimiques aptes à graver sensiblement

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le matériau constituant la couche enterrée. L'étape a) comprend la formation sur la couche enterrée d'une couche de protection, elle aussi enterrée, en un matériau choisi pour résister suffisamment à l'attaque chimique d'espèces chimiques du traitement mis en œuvre lors de l'étape b), condamnant ainsi des accès possibles à la couche enterrée par lesquels ces espèces pourraient s'infiltrer. L'invention concerne en outre une application du procédé à la réalisation de structures destinées à l'électronique, l'optique ou l'optoélectronique.